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FDA24N50 N-Channel UniFETTM MOSFET 500 V, 24 A, 190 mΩ

Features

- $R_{DS(on)}$ = 160 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 12 A
- Low Gate Charge (Typ. 65 nC)
- Low C_{rss} (Typ. 35 pF)
- 100% Avalanche Tested
- RoHS Compliant

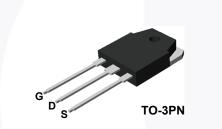
Applications

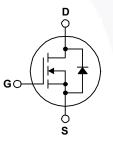
- PDP TV
- Uninterruptible Power Supply
- AC-DC Power Supply

FDA24N50 — N-Channel UniFETTM MOSFET

Description

UniFETTM MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

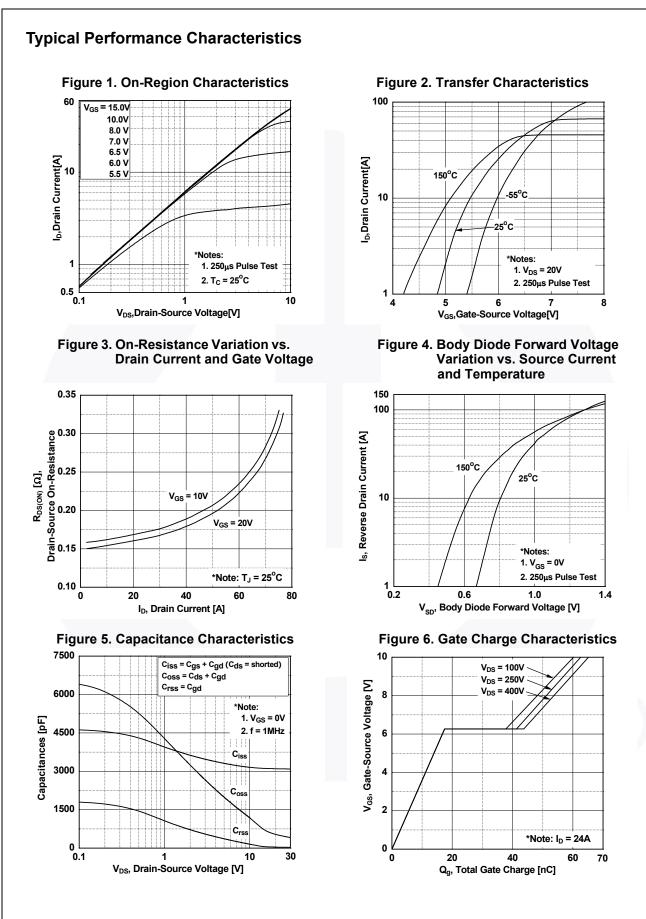
Symbol		Parameter			Unit	
V _{DSS}	Drain to Source Voltage			500	V	
V _{GSS}	Gate to Source Voltage	Gate to Source Voltage			V	
ID	Drain Current	- Continuous (T _C = 25 ^o C)		24	•	
		- Continuous (T _C = 100 ^o C)		14	A	
I _{DM}	Drain Current	- Pulsed (Note 1)	96	Α	
E _{AS}	Single Pulsed Avalanche Energy (Note 2)			1872	mJ	
I _{AR}	Avalanche Current	(Note 1)	24	Α	
E _{AR}	Repetitive Avalanche En	ergy (Note 1)	27	mJ	
dv/dt	Peak Diode Recovery dv/dt (Note 3)		Note 3)	4.5	V/ns	
P _D	Power Dissipation	(T _C = 25°C)		270	W	
		- Derate Above 25°C		2.2	W/ºC	
T _J , T _{STG}	Operating and Storage Temperature Range			-55 to +150	°C	
TL	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds			300	°C	

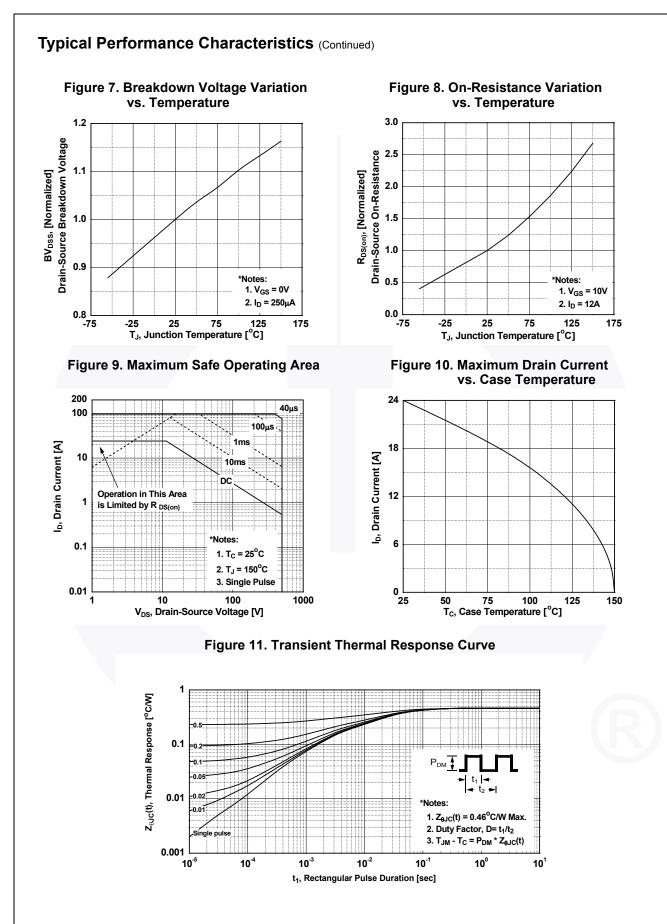
Thermal Characteristics

Symbol	Parameter	FDA24N50	Unit
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction to Case, Max.	0.46	°C/W
$R_{ hetaJA}$	Thermal Resistance, Junction to Ambient, Max.	40	°C/vv

FDA24N50
— N-Channel
UniFET TM I
MOSFET

Part Nu	mber	Top Mark	Package	Packing Method	Reel Size	T	ape Width	Qua	Quantity	
FDA24	N50	FDA24N50	TO-3PN	Tube	N/A		N/A	30 units		
Electrica	al Chara	acteristics T _C = 25°C	unless othe	erwise noted.						
Symbol		Parameter		Test Condition	S	Min.	Тур.	Max.	Unit	
Off Charac	teristics						<u> </u>			
BV _{DSS}	Drain to Source Breakdown Voltage		In =	I _D = 250 μA, V _{GS} = 0 V, T _J = 25 ^o C			-	-	V	
ΔBV _{DSS} / ΔT _J		Breakdown Voltage Temperature Coefficient		$I_D = 250 \ \mu A$, Referenced to $25^{\circ}C$			0.66	-	V/ºC	
I _{DSS}	Zero Gate Voltage Drain Current			$V_{DS} = 500 V, V_{GS} = 0 V$ $V_{DS} = 400 V, T_{C} = 125^{\circ}C$				1 10	μA	
I _{GSS}	Gate to B	ody Leakage Current	V _G	$_{\rm S}$ = ±30 V, V _{DS} = 0 V		-	-	±100	nA	
On Charac	toristics									
V _{GS(th)}		eshold Voltage	Va	_S = V _{DS} , I _D = 250 μA		3.0	-	5.0	V	
R _{DS(on)}		ain to Source On Resistance		$s = 10 \text{ V}, I_D = 12 \text{ A}$		-	0.16	0.19	Ω	
9 _{FS}	Forward	Transconductance		_S = 20 V, I _D = 12 A		-	28	-	S	
Dynamic C	`haractor	istice		5			11			
C _{iss}	Input Cap					-	3120	4150	pF	
C _{oss}		apacitance		$V_{DS} = 25 V, V_{GS} = 0 V,$ f = 1 MHz $V_{DS} = 400 V, I_D = 24 A,$ V_{GS} = 10 V		_	460	615	pF	
C _{rss}		Transfer Capacitance	f =			-	35	52	pF	
Q _{g(tot)}		e Charge at 10V	V-			-	65	85	nC	
Q _{gs}		ource Gate Charge				-	18	-	nC	
Q _{gd}		rain "Miller" Charge	0		(Note 4)	-	26	-	nC	
Switching	Characte	eristics								
t _{d(on)}		Delay Time				-	47	104	ns	
t _r		Rise Time	VDI	V_{DD} = 250 V, I _D = 24 A, V _{GS} = 10 V, R _G = 25 Ω (Note 4)		-	108	226	ns	
t _{d(off)}		Delay Time	V _G			-	164	338	ns	
t _f	Turn-Off F	•				- 1	86	182	ns	
·		Characteristics							-	
		e Characteristics		and Ormant			I I I I I I I I I I I I I I I I I I I	04		
I _S		Continuous Drain to Source				-	-	24	A	
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current				-	-	96	A V		
V _{SD}		in to Source Diode Forward Voltage rerse Recovery Time rerse Recovery Charge		$V_{GS} = 0 V, I_{SD} = 24 A$ $V_{GS} = 0 V, I_{SD} = 24 A,$ $dI_F/dt = 100 A/\mu s$		-	- 540	1.4	v ns	
t _{rr} Q _{rr}						-	8.1	<u> </u>	μC	
		, ,	·						1 1.0	
Notes: 1. Repetitive rating 2. L = 6.5 mH, I _{AS} 3. I _{SD} ≤ 24 A, di/dt	= 24 A, V _{DD} = ξ ≤ 200 A/μs, V _D	nited by maximum junction temperat 50 V, $R_G = 25 \Omega$, starting $T_J = 25^{\circ}C$. $_D \le BV_{DSS}$, starting $T_J = 25^{\circ}C$. rating temperature typical characteris						E		



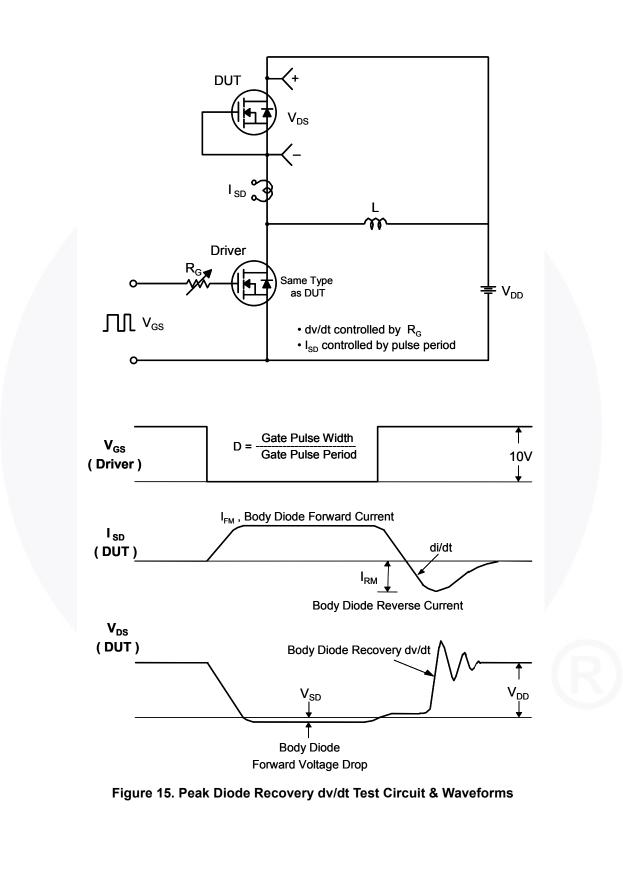


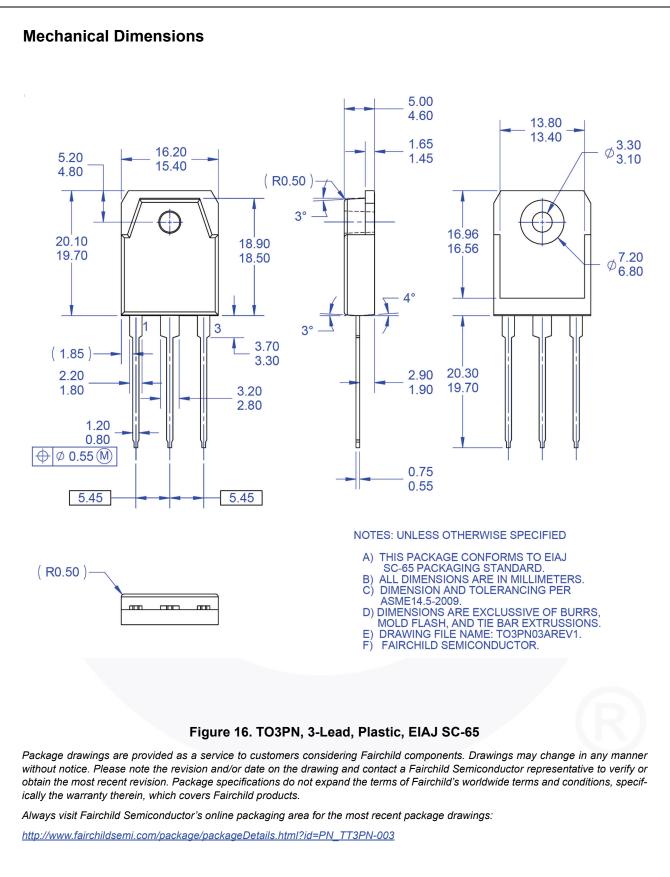
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 V_{GS} ξ ק Q_g V_{DS} Q_{gd} Q_{gs} • DUT I_G = const. Charge Figure 12. Gate Charge Test Circuit & Waveform R VDS V_{DS} 90% ο V_{DD} GS R_{G} 10% V_{GS} DUT V_{GS} ∏ o Figure 13. Resistive Switching Test Circuit & Waveforms L $E_{AS} = \frac{1}{2} L I_{AS}^2$ V_{DS} $\mathsf{BV}_{\mathsf{DSS}}$ ID o AS R_G **∔** ∨_{DD} $I_D(t)$ V_{GS} $V_{DS}(t)$ V_{DD} DUT Time t_p Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

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